

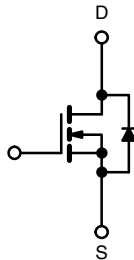
N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
80	0.0048 at $V_{GS} = 10$ V	120 ^a	161 nC



Top View



N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/AC Inverters
- LED Backlighting


RoHS
 COMPLIANT

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	120 ^a	A
	$T_C = 70$ °C	92	
	$T_A = 25$ °C	35 ^b	
	$T_A = 70$ °C	21 ^b	
Pulsed Drain Current ($t = 100$ μ s)	I_{DM}	460	mJ
Continuous Source-Drain Diode Current	$T_C = 25$ °C	120 ^a	
	$T_A = 25$ °C	15 ^b	
Single Pulse Avalanche Current	$L = 0.1$ mH	110	
Single Pulse Avalanche Energy	E_{AS}	1450	W
Maximum Power Dissipation	$T_C = 25$ °C	255	
	$T_C = 70$ °C	160	
	$T_A = 25$ °C	5 ^b	
	$T_A = 70$ °C	3.3 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	10	16	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.50	0.68	

Notes

- a. Package limited.
 b. Surface mounted on 1" x 1" FR4 board.

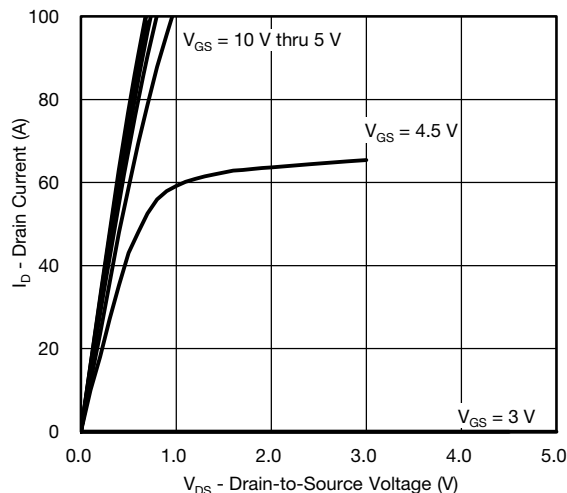
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	80			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		37		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5		3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 64 V, V _{GS} = 0 V			1	μA
		V _{DS} = 64 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	460			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 40 A		0.0048	0.006	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 25 V, I _D = 20 A		90		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} =64 V, V _{GS} = 0 V, f = 1 MHz		6255		pF
Output Capacitance	C _{oss}			550		
Reverse Transfer Capacitance	C _{rss}			366		
Total Gate Charge	Q _g	V _{DS} = 64 V, V _{GS} = 10 V, I _D = 40 A		161		nC
		V _{DS} = 64 V, V _{GS} = 6 V, I _D = 30 A		95		
		V _{DS} = 64 V, V _{GS} = 4.5 V, I _D = 20 A		80		
Gate-Source Charge	Q _{gs}			33		
Gate-Drain Charge	Q _{gd}			12		
Output Charge	Q _{oss}	V _{DS} = 50 V, V _{GS} = 0 V		61		
Gate Resistance	R _g	f = 1 MHz		1.5		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		24		ns
Rise Time	t _r			20		
Turn-Off DelayTime	t _{d(off)}			83		
Fall Time	t _f			28		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 6.0 V, R _g = 1 Ω		25		
Rise Time	t _r			73		
Turn-Off DelayTime	t _{d(off)}			34		
Fall Time	t _f			28		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}				460	
Body Diode Voltage	V _{SD}	I _S = 5 A		0.7	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		39		ns
Body Diode Reverse Recovery Charge	Q _{rr}			32		nC
Reverse Recovery Fall Time	t _a			20		ns
Reverse Recovery Rise Time	t _b			19		

Notes

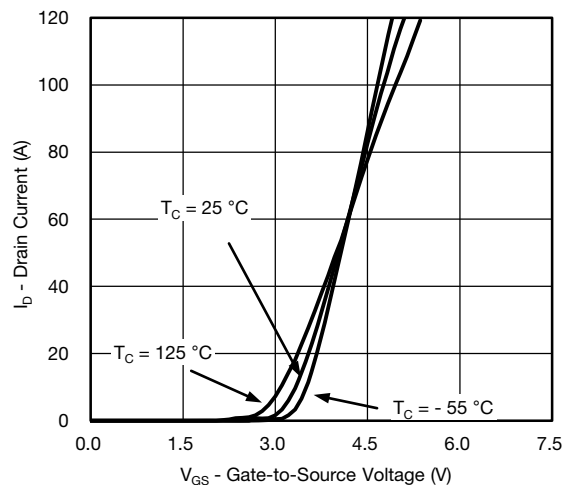
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

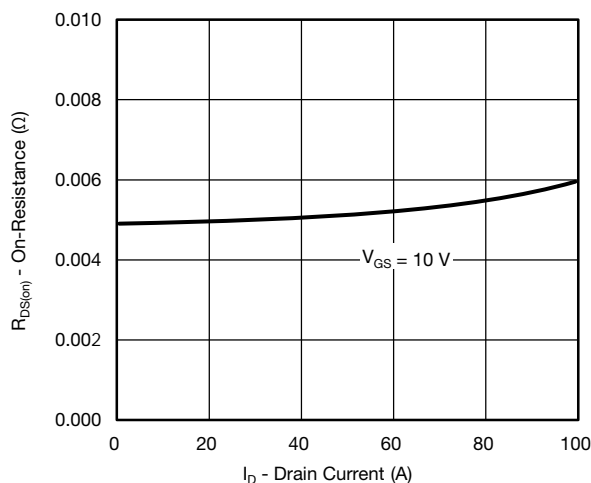
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



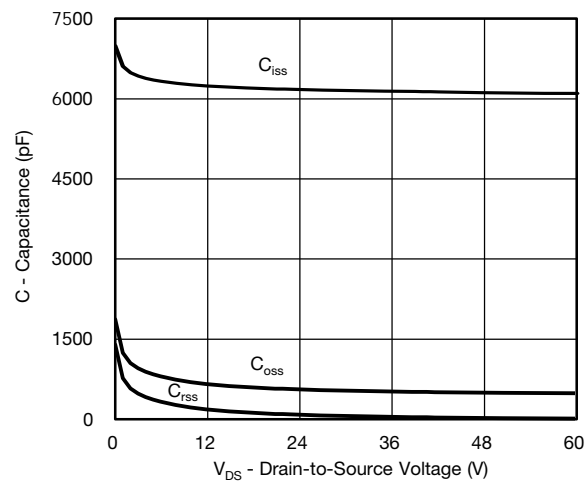
Output Characteristics



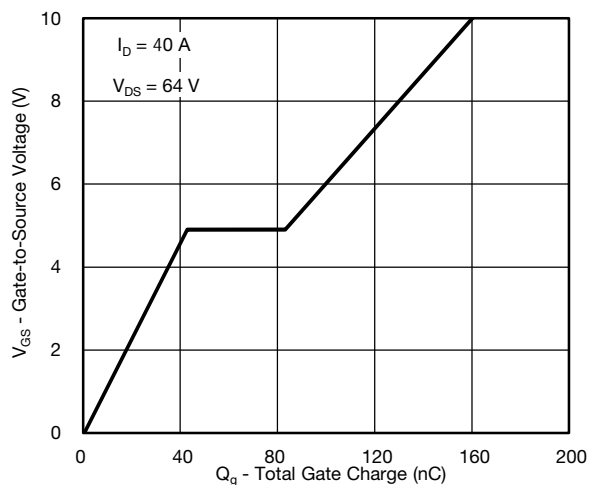
Transfer Characteristics



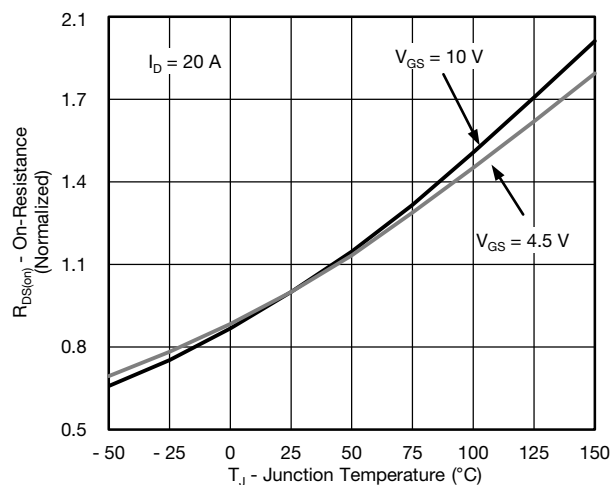
On-Resistance vs. Drain Current



Capacitance

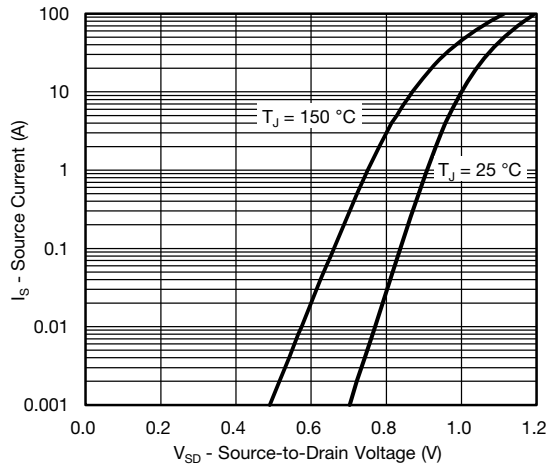


Gate Charge



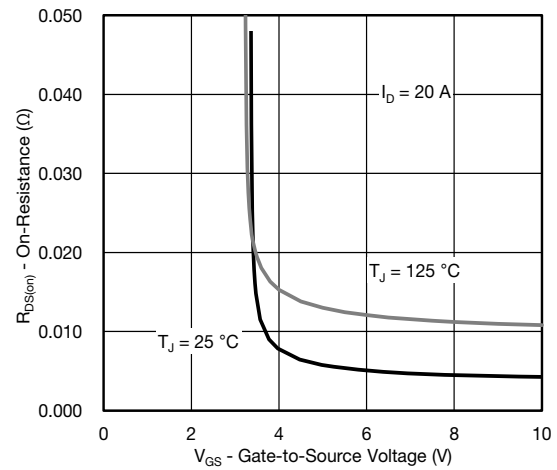
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

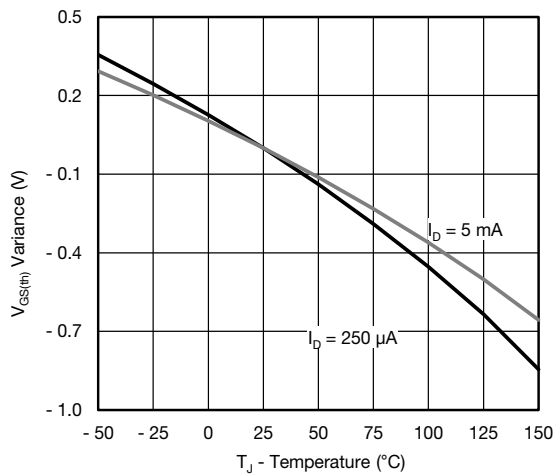


Source-Drain Diode Forward Voltage

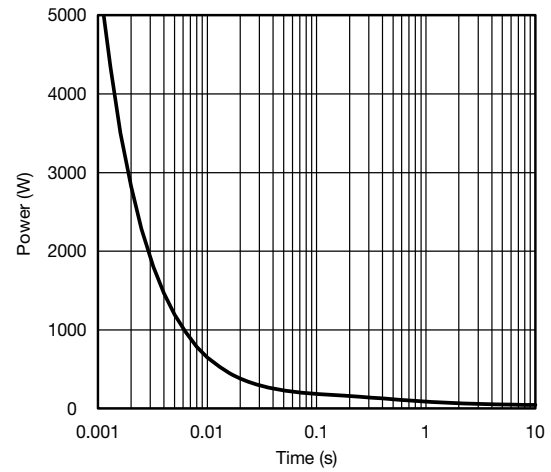
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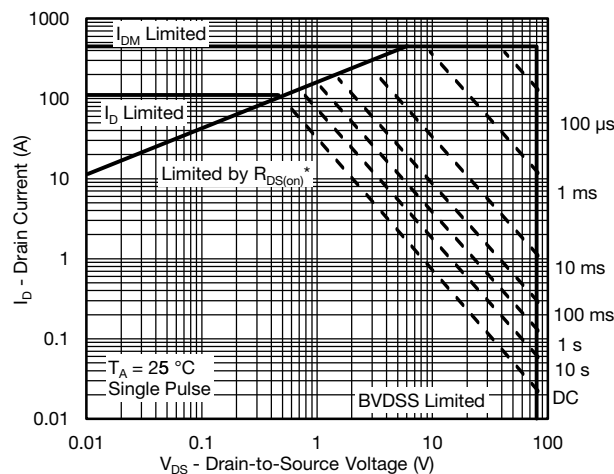
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



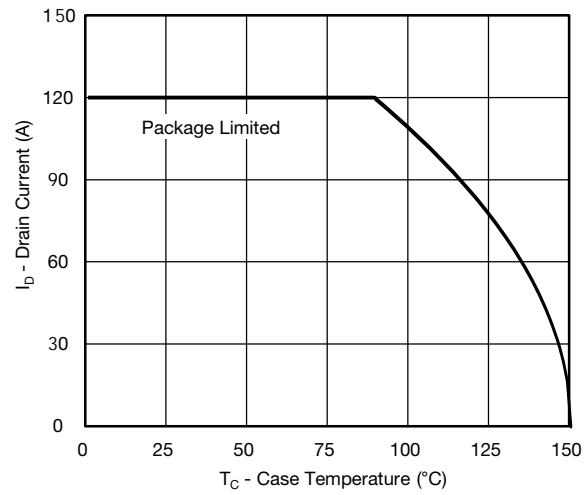
Single Pulse Power, Junction-to-Ambient



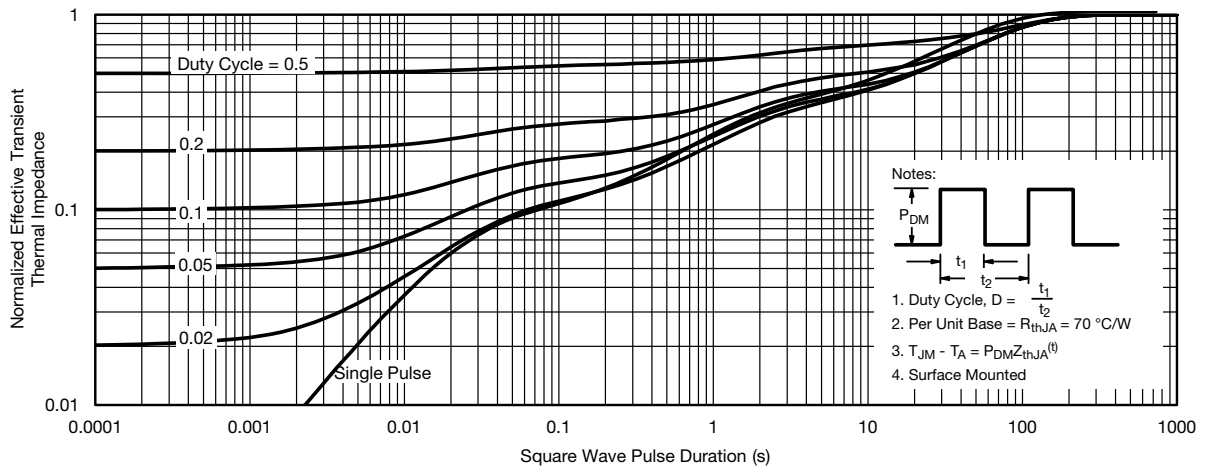
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



Normalized Thermal Transient Impedance, Junction-to-Ambient

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